Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application:

Listing of the Claims:

1. (Currently Amended) A field effect transistor, comprising:

a substrate having a recess in a surface thereof, the recess having a bottom portion and substantially vertical sidewalls;

a gate dielectric layer disposed superjacent the bottom portion of the recess, ~~and~~ adjacent the substantially vertical sidewalls, and superjacent a portion of a top surface of the substrate;

a gate electrode completely overlying the gate dielectric layer; and

source/drain terminals disposed in the substrate in alignment with a pair of laterally opposed gate electrode sidewalls, said gate electrode extending to a less shallow depth within said substrate than a depth at which the source/drain terminals are disposed;

wherein the source/drain terminals comprise an extension which extends to a more shallow depth within the substrate than the source/drain terminals to which it corresponds and extends downwardly, from approximately the surface of the substrate, along the sidewalls of the recess, ~~an entire innermost side of the extension is adjacent to the vertical sidewalls of the recess,~~ a portion of the gate dielectric layer overlaying an innermost portion of the extension.

2. (Previously Presented) The transistor of Claim 1, further comprising a portion of the gate electrode that overlies the innermost portion of the extension.

3. (Previously Presented) The transistor of Claim 2, wherein the gate electrode conforms to a recessed channel.

4. (Currently Amended) A field effect transistor, comprising:

a substrate having a recess in a surface thereof, the recess having bottom portion and tapered sidewalls, the tapered sidewall surfaces forming an obtuse angle with respect to the bottom portions of the recess;

a gate dielectric layer disposed superjacent the bottom portion of the recess, ~~and~~ adjacent the tapered sidewalls, and superjacent a portion of a top surface of the substrate;

a gate electrode completely overlying the gate dielectric layer; and

source/drain terminals disposed in the substrate in alignment with a pair of laterally opposed gate electrode sidewalls;

wherein the source/drain terminals comprise an extension which extends to a more shallow depth within the substrate than the source/drain terminals to which it corresponds and extends downwardly, from approximately the surface of the substrate, along the sidewalls of the recess, ~~an entire innermost side of the extension is adjacent to the tapered sidewalls of the recess,~~ a portion of the gate dielectric layer overlaying an inner-most portion of the extension.

5. (Previously Presented) The transistor of Claim 4, wherein a portion of the gate electrode overlies an innermost portion of the extension.

6. (Previously Presented) The transistor of Claim 4, wherein the gate electrode conforms to a recessed channel.

7. (Currently Amended) A field effect transistor, comprising:

a substrate having a recess in a surface thereof, the recess having a curvilinear shape;

a gate dielectric layer disposed superjacent the curvilinear recess and superjacent a portion of a top surface of the substrate;

a gate electrode completely overlying the gate dielectric layer; and source/drain terminals disposed in the substrate in alignment with a pair of laterally opposed gate electrode sidewalls; and

wherein the source/drain terminals comprise an extension which extends to a more shallow depth within the substrate than the source/drain terminals to which it corresponds and extends downwardly, from approximately the surface of the substrate, along the curvilinear sides of the recess, a portion of the gate dielectric layer overlaying an inner-most portion of the extension.

8. (Previously Presented) The transistor of Claim 7, wherein the gate electrode conforms to a recessed channel.

9. (Previously Presented) The transistor of Claim 7, wherein the gate electrode conforms to a recessed channel.